

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	("5608572" "6026110" "6614059").PN. OR ("6853661").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2005/10/21 13:11
L4	3	((quantum near2 well) or QW) with stain\$3) and laser and active and (QW or (quantum near2 well)) and clad\$4 and substrate and barrier and guide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 13:21
L5	463	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and laser and active and (QW or (quantum near2 well)) and clad\$4 and substrate and barrier and guide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 13:25
L6	112	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and laser and active and (QW or (quantum near2 well)) and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and guide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 13:36
L7	10	6 and (guide with (AlGaAs or "Al" near5 "Ga" near5 "As"))	USPAT	AND	ON	2005/10/21 13:27
L8	27	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((semiconductor or diode or VCSEL) near4 laser) and active and (QW or (quantum near2 well)) and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide with (AlGaAs or "Al" near5 "Ga" near5 "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 13:47
L9	0	JP2002006271	JPO	AND	ON	2005/10/21 13:34
L10	2	"2002006271"	JPO	AND	ON	2005/10/21 13:44
L11	27	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and laser and active and (QW or (quantum near2 well)) and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and guide and (guide with (AlGaAs or "Al" near5 "Ga" near5 "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 13:42
L12	27	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and laser and active clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide with (AlGaAs or "Al" near5 "Ga" near5 "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 13:43
L13	0	"2001384511"	JPO	AND	ON	2005/10/21 13:44
L14	1	jp2001384511	JPO	AND	ON	2005/10/21 13:58
L17	43	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and guide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 13:50
L18	15	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide with (AlGaAs or "Al" near5 "Ga" near5 "As"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 14:00
L19	0	jp2002006271	JPO	AND	ON	2005/10/21 13:58
L20	2	"2002006271"	JPO	AND	ON	2005/10/21 13:58
L21	37	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 14:03

L24	22	21 not 18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 14:04
L25	37	((quantum near2 well)-or QW or quantum-well) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 14:03
L26	22	25 not 18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/21 14:04